



## 800mA STEP-DOWN DC-DC CONVERTER

## Description

The PAM2301 is a step-down current-mode, DC-DC converter. At heavy load, the constant frequency PWM control performs excellent stability and transient response. To ensure the longest battery life in portable applications, the PAM2301 provides a power-saving Pulse-Skipping Modulation (PSM) mode to reduce quiescent current under light load operation to save power.

The PAM2301 supports a range of input voltages from 2.5V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, USB and other standard power sources. The output voltage is adjustable from 0.6V to the input voltage, while the part number suffix PAM2301-XX indicates pre-set output voltage of 3.3V, 1.2V or adjustable. All versions employ internal power switch and synchronous rectifier to minimize external part count and realize high efficiency. During shutdown, the input is disconnected from the output and the shutdown current is less than 0.1mA. Other key features include under-voltage lockout to prevent deep battery discharge.

The PAM2301 is available in TSOT25 package.

## Features

- Efficiency up to 96%
- Only 40µA (typical) Quiescent Current
- Output Current: Up to 800mA
- Internal Synchronous Rectifier
- 1.5MHz Switching Frequency
- Soft Start
- Under-Voltage Lockout
- Short Circuit Protection
- Thermal Shutdown
- TSOT25 Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





# Applications

- Cellular Phone
- Portable Electronics
- Wireless Devices
- Cordless Phone
- Computer Peripherals
- Battery-Powered Widgets
- Electronic Scales
- Digital Frame



# **Typical Applications Circuit**

### Fixed Output Voltage





Adjustable Output Voltage

## **Pin Descriptions**

| Pin Number | Pin Name | Function   |
|------------|----------|--|
| 1          | EN       | Enable Control Input. Force this pin voltage above 1.5V, enables the chip, and below 0.3V shuts down the device.   |
| 2          | GND      | Ground   |
| 3          | SW       | The drains of the internal main and synchronous power MOSFET.  |
| 4          | VIN      | Power Supply   |
| 5          | VOUT/FB  | <ul> <li>VOUT: Output voltage feedback pin, an internal resistive divider divides the output voltage down for comparison to the internal reference voltage.</li> <li>FB: Feedback voltage to internal error amplifier, the threshold voltage is 0.6V.</li> </ul> |

# **Functional Block Diagram**





## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability. All voltages are with respect to ground.

| Parameter                 | Rating                          | Unit       |  |  |
|---------------------------|---------------------------------|------------|--|--|
| Input Voltage             | -0.3 to +6.0                    | V          |  |  |
| EN, FB Pin Voltage        | -0.3 to V <sub>IN</sub>         | V          |  |  |
| SW Pin Voltage            | -0.3 to (V <sub>IN</sub> + 0.3) | V          |  |  |
| Junction Temperature      | +150                            | ٦°         |  |  |
| Storage Temperature Range | -65 to +150                     | <b>O</b> ° |  |  |
| Soldering Temperature     | +300, 5s                        | C°         |  |  |

## Recommended Operating Conditions (@TA = +25°C, unless otherwise specified.)

| Parameter                   | Rating      |        | Unit |
|-----------------------------|-------------|--------|------|
| Supply Voltage              | 2.5 to 5.5  | $\sim$ | V    |
| Operation Temperature Range | -40 to +85  |        | °C   |
| Junction Temperature Range  | -40 to +125 |        |      |
|                             |             |        |      |

# **Thermal Information**

|  |        |     | *    |
|--|--------|-----|------|
| Parameter                                | Symbol | Мах | Unit |
| Thermal Resistance (Junction to Case)    | θ」C    | 130 | °C/W |
| Thermal Resistance (Junction to Ambient) | θ」ር    | 250 | 0.00 |
| Internal Power Dissipation               | PD     | 400 | mW   |
|  |        |     |      |

# Electrical Characteristics (@T<sub>A</sub> = +25°C, V<sub>IN</sub> = 3.6V, V<sub>O</sub> = 1.8V, C<sub>IN</sub> = 10µF, L = 4.7µH unless otherwise specified.)

| Parameter                         | Parameter Symbol Test Conditions |  | Min      | Тур   | Max   | Units |     |
|-----------------------------------|----------------------------------|--|----------|-------|-------|-------|-----|
| Input Voltage Range               | V <sub>IN</sub>                  | -  |          | 2.5   | _     | 5.5   | V   |
| Regulated Feedback Voltage        | V <sub>FB</sub>                  |  |          | 0.588 | 0.600 | 0.612 | V   |
| Reference Voltage Line Regulation | ΔV <sub>FB</sub>                 | -  |          |       | 0.3   |       | %/V |
| Regulated Output Voltage Accuracy | Vo                               | I <sub>O</sub> = 100mA   |          | -3    | _     | +3    | %   |
| Peak Inductor Current             | I <sub>PK</sub>                  | V <sub>IN</sub> = 3V, V <sub>FB</sub> = 0.5V or V <sub>O</sub> = 90% |          |       | 1.2   |       | А   |
| Output Voltage Line Regulation    | -LNR                             | V <sub>IN</sub> = 2.5V to 5V, I <sub>O</sub> = 10mA                  |          | —     | 0.2   | 0.5   | %/V |
| Output Voltage Load Regulation    | LDR                              | I <sub>O</sub> = 1mA to 800mA  |          | —     | 0.5   | 1.5   | %   |
| Quiescent Current                 | lq                               | No Load  |          | —     | 40    | 70    | μA  |
| Shutdown Current                  | I <sub>SD</sub>                  | V <sub>EN</sub> = 0V   |          |       | 0.1   | 1.0   | μA  |
|                                   | í.                               | V <sub>O</sub> = 100%  |          | 1.2   | 1.5   | 1.8   | MHz |
| Oscillator Frequency              | fosc                             | $V_{FB} = 0V \text{ or } V_O = 0V$                                   |          |       | 500   |       | kHz |
| Drain-Source On-State Resistance  | Provous                          | I <sub>DS</sub> = 100mA  | P MOSFET |       | 0.30  | 0.45  | Ω   |
|                                   | Rds(on)                          | IDS - TOOTTA   | N MOSFET | —     | 0.35  | 0.50  | Ω   |
| SW Leakage Current                | I <sub>LSW</sub>                 | —  |          | —     | ±0.01 | 1     | μA  |
| High Efficiency                   | η                                | —  |          | —     | 96    | _     | %   |
| EN Threshold High                 | V <sub>EH</sub>                  | —  |          | 1.5   | _     | _     | V   |
| EN Threshold Low                  | V <sub>EL</sub>                  | —  |          | _     | _     | 0.3   | V   |
| EN Leakage Current                | I <sub>EN</sub>                  | —  |          | —     | ±0.01 | _     | μA  |
| Over Temperature Protection       | OTP                              | —  |          | —     | +150  | —     | °C  |
| OTP Hysteresis                    | OTH                              | —  |          | —     | +30   | —     | °C  |



# **Typical Performance Characteristics** (@T<sub>A</sub> = +25°C, C<sub>IN</sub> = 10 $\mu$ F, C<sub>O</sub> = 10 $\mu$ F, L = 4.7 $\mu$ H, unless otherwise specified.)





# **Typical Performance Characteristics** (continued) (@ $T_A = +25^{\circ}C$ , $C_{IN} = 10\mu$ F, $C_O = 10\mu$ F, $L = 4.7\mu$ H, unless otherwise specified.)





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## Application Information

The basic PAM2301 application circuit is shown on Page 2. External component selection is determined by the load requirement, selecting L first and then C<sub>IN</sub> and C<sub>OUT</sub>.

#### **Inductor Selection**

For most applications, the value of the inductor will fall in the range of  $1\mu$ H to  $4.7\mu$ H. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V<sub>IN</sub> or V<sub>OUT</sub> also increases the ripple current as shown in Equation 1. A reasonable starting point for setting ripple current is  $\Delta$ I<sub>L</sub> = 320mA (40% of 800mA).

$$\Delta I_{L} = \frac{1}{(f)(L)} V_{OUT} \left( 1 - \frac{V_{OUT}}{V_{IN}} \right)$$
 Equation 1

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, the 1120mA rated inductor should be enough for most applications (800mA + 320mA). For better efficiency, choose a low DC-resistance inductor.

### CIN and COUT Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle V<sub>OUT</sub>/V<sub>IN</sub>. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{IN}$$
 required  $I_{RMS} \cong I_{OMAX} \frac{\left[V_{OUT} \left(V_{IN} - V_{OUT}\right)\right]^{1/2}}{V_{IN}}$ 

This formula has a maximum at  $V_{IN} = 2V_{OUT}$ , where  $I_{RMS} = I_{OUT}/2$ . This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Consult the manufacturer if there is any question.

The selection of COUT is driven by the required effective series resistance (ESR).

Typically, once the ESR requirement for C<sub>OUT</sub> has been met, the RMS current rating generally far exceeds the I<sub>RIPPLE</sub> (P-P) requirement. The output ripple V<sub>OUT</sub> is determined by:

$$vV_{OUT} \cong vI_{L}\left(ESR + \frac{1}{8fC_{OUT}}\right)$$

Where f = operating frequency,  $C_{OUT}$  = output capacitance and  $\Delta I_L$  = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since  $\Delta I_L$  increases with input voltage.

### Using Ceramic Input and Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

## Setting the Output Voltage

The internal reference is 0.6V (Typical). The output voltage is calculated as below:

$$V_0 = 0.6 \times \left(1 + \frac{R1}{R2}\right)$$

The output voltage is given by Table 1.

| Vo   | R1   | R2   |
|------|------|------|
| 1.2V | 100k | 100k |
| 1.5V | 150k | 100k |
| 1.8V | 200k | 100k |
| 2.5V | 380k | 120k |
| 3.3V | 540k | 120k |



## Application Information (continued)

#### 100% Duty Cycle Operation

As the input voltage approaches the output voltage, the converter turns the P-Channel transistor continuously on. In this mode the output voltage is equal to the input voltage minus the voltage drop across the P-Channel transistor:

 $V_{OUT} = V_{IN} - I_{LOAD} \times (R_{DS(ON)} + R_L)$ 

where R<sub>DS(ON)</sub> = P-Channel Switch ON Resistance, I = Output Current, R = Inductor DC Resistance.

#### UVLO AND Soft-Start

The reference and the circuit remain reset until the V<sub>IN</sub> crosses its UVLO threshold.

The PAM2301 has an internal soft-start circuit that limits the in-rush current during start-up. This prevents possible voltage drops of the input voltage and eliminates the output voltage overshoot. The soft-start acts as a digital circuit to increase the switch current in several steps to the P-Channel current limit (1500mA).

#### **Short Circuit Protection**

The switch peak current is limited cycle-by-cycle to a typical value of 1500mA. In the event of an output voltage short circuit, the device operates with a frequency of 400kHz and minimum duty cycle, therefore the average input current is typically 200mA.

#### Thermal Shutdown

When the die temperature exceeds +150°C, a reset occurs and the reset remains until the temperature decrease to 120°C, at which time the circuit can be restarted.

#### PCB Layout Check List

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the PAM2301. These items are also illustrated graphically in Figure 1. Check the following in your layout:

- 1. The power traces, consisting of the GND trace, the SW trace and the VIN trace should be kept short, direct and wide.
- 2. Does the V<sub>FB</sub> pin connect directly to the feedback resistors? The resistive divider R1/R2 must be connected between the (+) plate of C and ground.
- 3. Does the (+) plate of CIN connect to VIN as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.
- 4. Keep the switching node, SW, away from the sensitive VFB node.
- 5. Keep the (–) plates of  $C_{\mathsf{IN}}$  and  $C_{\mathsf{OUT}}$  as close as possible



Figure 1. PAM2301 Suggested Layout



## **Ordering Information**



Notes:

4

3

SW

BAVYW

2

GND

TSOT25

5

ΕN



- V: Output Voltage
- Y: Year
- W: Week



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.







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